

ABSTRACT OF THE DISCLOSURE

The object of the present invention is to lower the oscillation threshold value and to improve the yield by improving the luminous efficiency in the central wavelength of a laser. To achieve the object, the
5 nitride semiconductor light emitting element of the present invention includes a substrate, a lower clad layer formed of a nitride semiconductor containing Al and Ga formed thereon, a lower guide layer formed of a nitride semiconductor mainly containing In and Ga formed thereon, and an active layer including a nitride semiconductor mainly containing In and Ga formed
10 thereon. The lower guide layer has a first layer and a second layer higher in In content than the first layer, successively stacked from the active layer side.